

AMENDMENTS TO THE CLAIMS

Claim 1 (Currently Amended): A high concentration silica slurry, comprising:  
a silica powder dispersed in an solvent,  
said silica slurry having a silica concentration of more than 50 % by weight and a  
viscosity of less than 1000 mPa·s,  
wherein said silica powder has a ratio DL/DT of less than 1.3, wherein DL is an  
average particle size of the silica powder measured by a laser diffraction particle size  
distribution method and DT is an average primary particle size of the silica powder measured  
by a TEM photography observation, and  
wherein said silica powder has an average primary particle size of from 0.08 $\mu\text{m}$  to  
0.8 $\mu\text{m}$ ,  
wherein said silica powder is fumed silica produced by a dry process, and  
wherein said silica powder has impurity concentrations of less than 1.0 ppm of each  
of sodium and potassium, less than 1.0 ppm of aluminum, and less than 5 ppm of each of  
sulfur, nickel, chromium, and iron.

Claim 2 (Original): The high concentration silica slurry according to Claim 1,  
wherein the silica concentration is from more than 70 % by weight to less than 80 % by  
weight and the viscosity is less than 800 mPa·s at the time of preparing.

Claim 3 (Original): The high concentration silica slurry according to Claim 1,  
wherein a ratio B/A is less than 1.5, wherein A is the viscosity of the slurry measured at the  
time of preparing and B is the viscosity after one month.

**Claim 4 (Canceled)**

**Claim 5 (Original):** The high concentration silica slurry according to Claim 1, wherein said solvent is water.

**Claim 6 (Original):** The high concentration silica slurry according to Claim 1, wherein at least two silica powders with different particle sizes are used.

**Claim 7 (Original):** A polishing composite, comprising:  
the high concentration silica slurry according to Claim 1.

**Claim 8 (Original):** The polishing composite according to Claim 7, wherein the silica concentration is from more than 70 % by weight to less than 80 % by weight and the viscosity is less than 800 mPa·s at the time of preparing.

**Claim 9 (Original):** The polishing composite according to Claim 7, wherein a ratio B/A is less than 1.5, wherein A is the viscosity of the slurry measured at the time of preparing and B is the viscosity after one month.

**Claim 10 (Original):** The polishing composite according to Claim 7, wherein the impurity concentrations of said silica powder are less than 1.0 ppm of each of sodium and potassium, less than 1.0 ppm of aluminum, and less than 5 ppm of each of sulfur, nickel, chromium, and iron.

Claim 11 (Original): The polishing composite according to Claim 7, wherein said solvent is water.

Claim 12 (Original): The polishing composite according to Claim 7, wherein at least two silica powders with different particle sizes are used.

Claim 13 (Original): A process for polishing a substrate, comprising:  
contacting the surface of said substrate with the slurry according to Claim 1.

Claim 14 (Original): The process according to Claim 13, wherein said substrate is a silicon wafer.

Claim 15 (Original): The process according to Claim 13, wherein the silica concentration is from more than 70 % by weight to less than 80 % by weight and the viscosity is less than 800 mPa•s at the time of preparing.

Claim 16 (Original): The process according to Claim 13, wherein a ratio B/A is less than 1.5, wherein A is the viscosity of the slurry measured at the time of preparing and B is the viscosity after one month.

Claim 17 (Original): The process according to Claim 13, wherein impurity concentrations of said silica powder are less than 1.0 ppm of each of sodium and potassium, less than 1.0 ppm of aluminum, and less than 5 ppm of each of sulfur, nickel, chromium, and iron.

Claim 18 (Original): The process according to Claim 13, wherein said solvent is water.

Claim 19 (Original): The process according to Claim 13, wherein at least two silica powders with different particle sizes are used.

Claim 20 (Original): The process according to Claim 13, wherein said substrate is a semiconductor material.